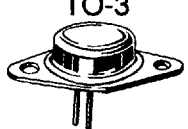
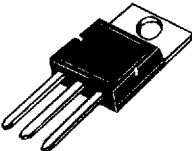


## DARLINGTON TRANSISTORS

Type	V <sub>CBO</sub> (V)	V <sub>CEO</sub> (V)	I <sub>C</sub> (A)	P <sub>tot</sub> (W)	V <sub>CEsat</sub> (V)	at I <sub>C</sub> / I <sub>B</sub> (A) (A)	Case JEDEC
BU 920	400	350	10	120	1.8	7 / 0.14	
BU 921	450	400	10	120	1.8	7 / 0.14	
BU 920 P	400	350	10	105	1.8	7 / 0.14	
BU 921 P	450	400	10	105	1.8	7 / 0.14	
BU 921 HP	450	400	15	105	2.0	7 / 0.15	

## POWER MODULES FOR SELF-COMMUTATED CONVERTERS

Type	V <sub>CBO</sub> (V)	V <sub>CEO</sub> (V)	I <sub>C</sub> (A)	I <sub>CM</sub> (A)	V <sub>CE(sat)</sub> (V)	t <sub>f</sub> (μs)	t <sub>on</sub> (μs)	t <sub>s</sub> (μs)	h <sub>21E</sub> (U <sub>CE</sub> =5V)	V <sub>F</sub> Diode (V)	R <sub>thjCT</sub> (K/W)	Case JEDEC
LS 2A 30/1000D	1000	800	30	60	<2.5	<3	<2.5	<15	>100	<1.2	<0.40	MO 2
LS 2A 50/1000D dual pack	1000	800	50	100	<2.5	<3	<2.5	<15	>100	<1.2	<0.31	MO 2
LS 1A 30/1000D	1000	800	30	60	<2.5	<3	<2.5	<15	>100	<1.2	<0.40	MO 2
LS 1A 50/1000D	1000	800	50	100	<2.5	<3	<2.5	<15	>100	<1.2	<0.31	MO 2
LS 1A 100/1000D Single	1000	800	100	200	<2.5	<3	<2.5	<15	>100	<1.2	<0.18	MO 2

bipolar transistors  
 insulated type darlington module with integrated reverse diode  
 Data per transistor, insulation voltage 2500 V.A.C., 1 min.

$U_{CEsat}$  at  $I_C$

$t_{on}$ ,  $t_s$ ,  $t_f$  at  $I_C$ , R-Load  $U_{CC} = 250V$

$h_{21E}$  at  $I_C$ ,  $U_{CE} = 5V$

$U_F$  at  $I_F = -I_C$